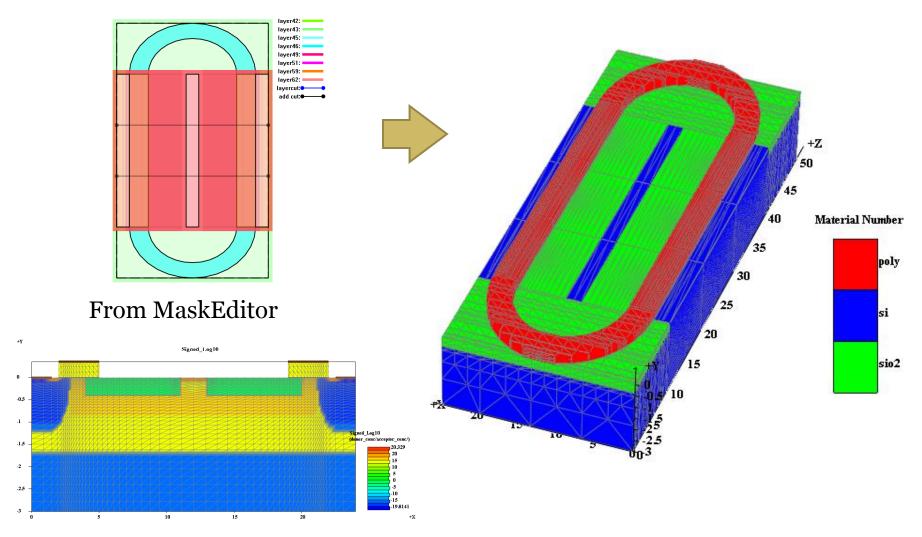


Power Semiconductor Devices Simulation with Crosslight TCAD Tools

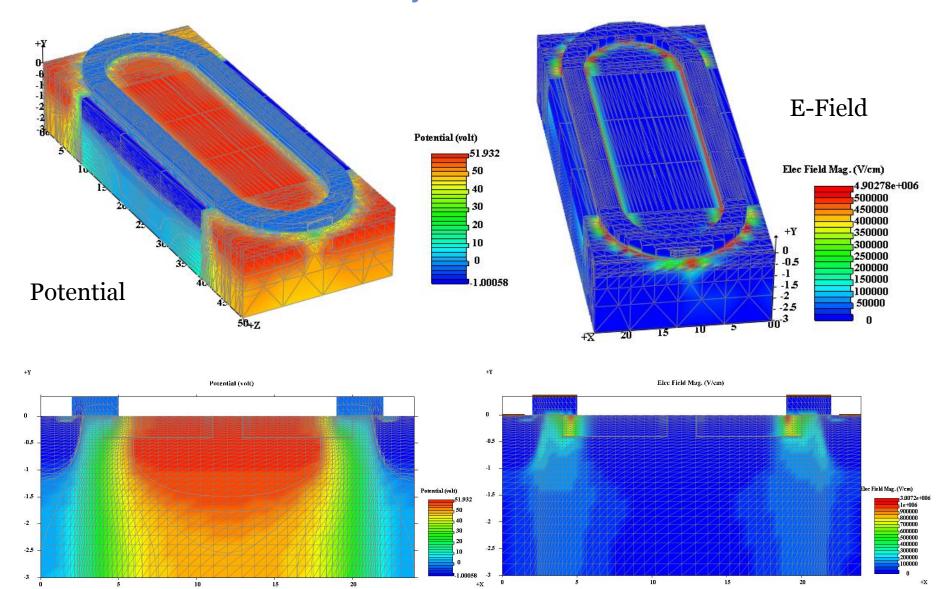
LDMOS with Race Track Poly Gate



CSuprem Simulation Result



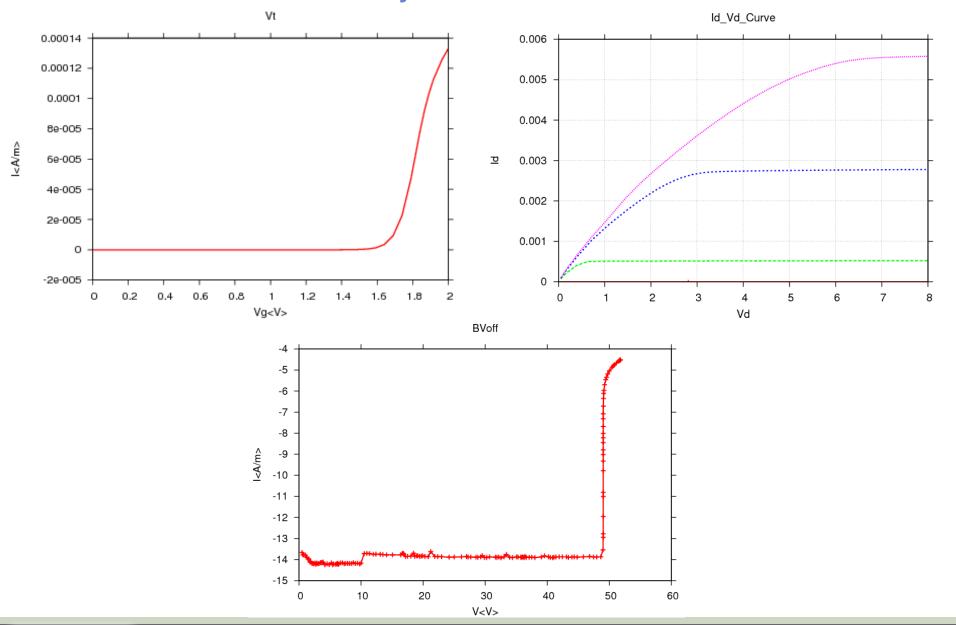
LDMOS with Race Track Poly Gate



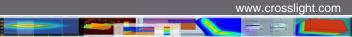




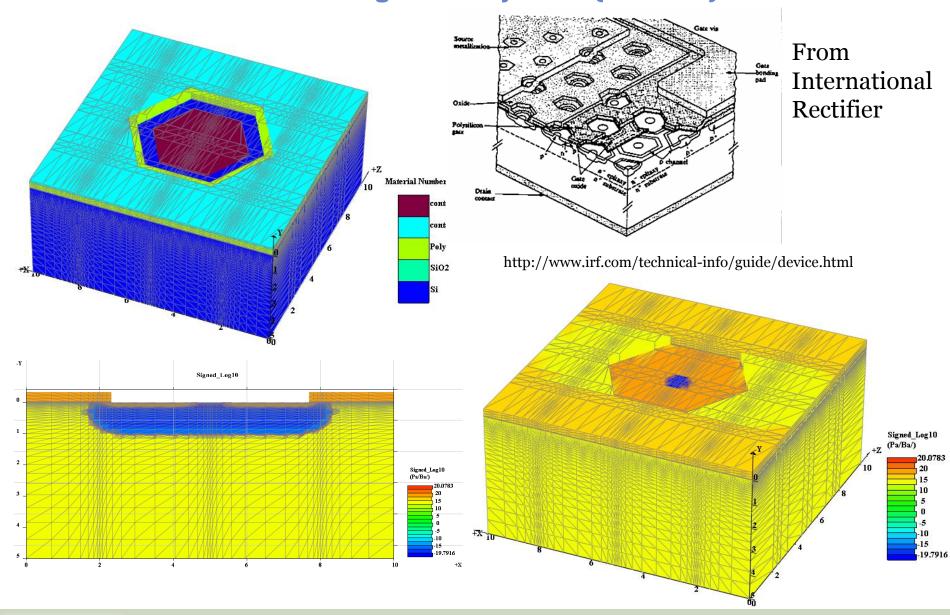
LDMOS with Race Track Poly Gate





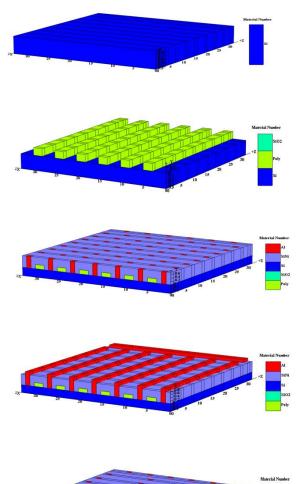


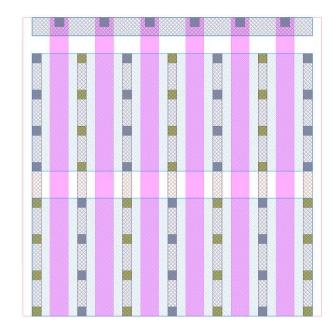
Vertical DMOS with Hexagonal Poly Gate (HexFET)

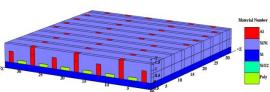


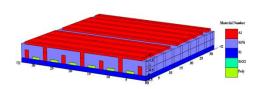
www.crosslight.com

Interconnect





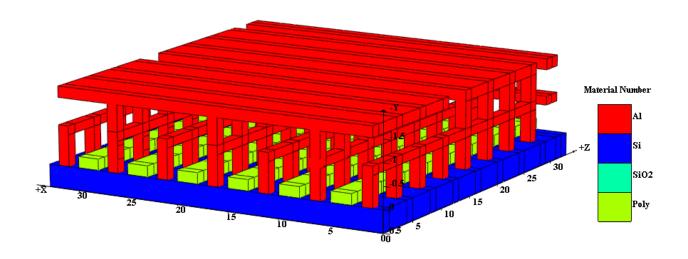


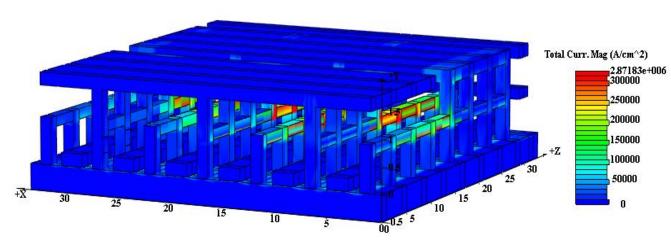




1-Active 2-Poly 3-Contact 4-Metal1 5-Via1 6-Metal2

Interconnect





Current magnitude plot



Interconnect Signed_Log10 (Pa/Ba/) 20.5461 20 15 - MOSFET Rdson 0.016 Interconnect Resistance Only -10 -15 0.014 16.2661 0.012 0.010 **Interconnect Simulation with MOSFET Devices** 0.008 0.006 0.004 0.002 0.000 0.02 0.06 0.08 0.10 Signed Log10 Vd (V) (Pa/Ba/) Comparing Rdson with and without MOSFET -10 19.9875

Interconnect Simulation without MOSFET Devices

